IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

IONESCU et al

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Examiner:

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September 16, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

As suggested by 37 C.F.R. 1.97, the undersigned attorney brings to the attention of the Patent and Trademark Office the references listed on the attached form PTO-1449, copies of non-U.S documents are enclosed. This is not to be construed as a representation that a search has been made or that no better prior art exists, or that a reference is relevant merely because cited.

Also enclosed is a copy of an International Search Report.

The Examiner is requested to initial the attached form PTO-1449 and to return a copy of the initialed document to the undersigned as an indication that the attached references have been considered and made of record.

IONESCU et al Serial No. Unknown



Respectfully submitted,

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INFORMATION DISCLOSURE CITATION

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